2SB1260

Rev.E Mar.-2016

ˇYت / Descriptions

SOT-89 PNP Silicon PNP transistor in a SOT-89 Plastic Package.

◕ Ȅ / Features

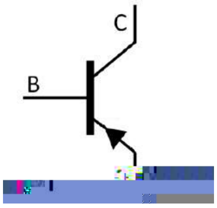
2SD1898

High breakdown voltage, good h_{FE} linearity, low $V_{CE(sat)}$, complements the 2SD1898.

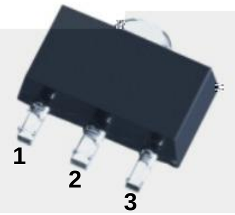
٧ ي / Applications

General power amplifier applications.

ŋ ڤ ặ ؍ ع / Equivalent Circuit



ẫ ﻻ ữ / Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

ƚ ӊ ڎ / Marking

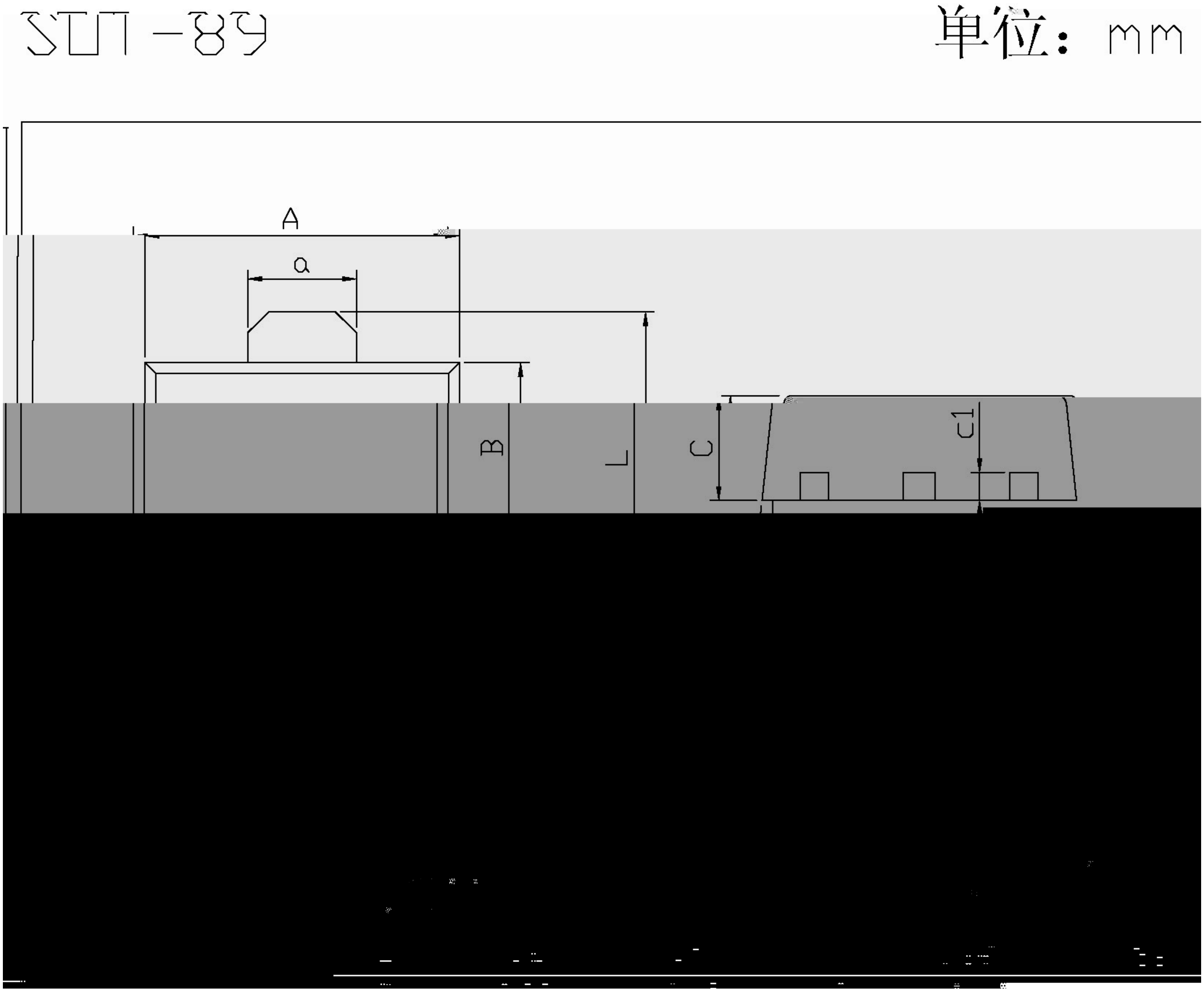
h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82˙ 180	120˙ 270	180˙ 390
Marking	HBHP⁑	HBHQ⁑	HBHR⁑

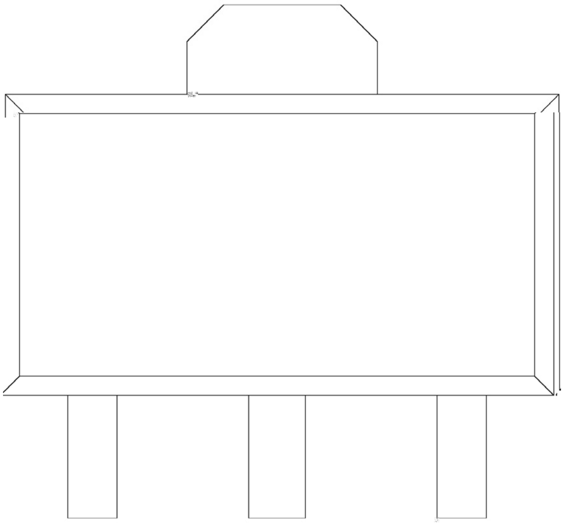
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-1.0	A
Collector Current-Continuous(Pulse)	$*I_{CP}$	-2.0	A
Collector Power Dissipation	$**P_C$	0.5	W
	$*P_C$	2.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55˙ 150	

*Single pulse Pw=100ms' 100ms Â
**mounted on 40×40×0.7mm ceramic board' 40×40×0.7m Â

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C				

ᵘ ẺỒḼ ʝ / Package Dimensions





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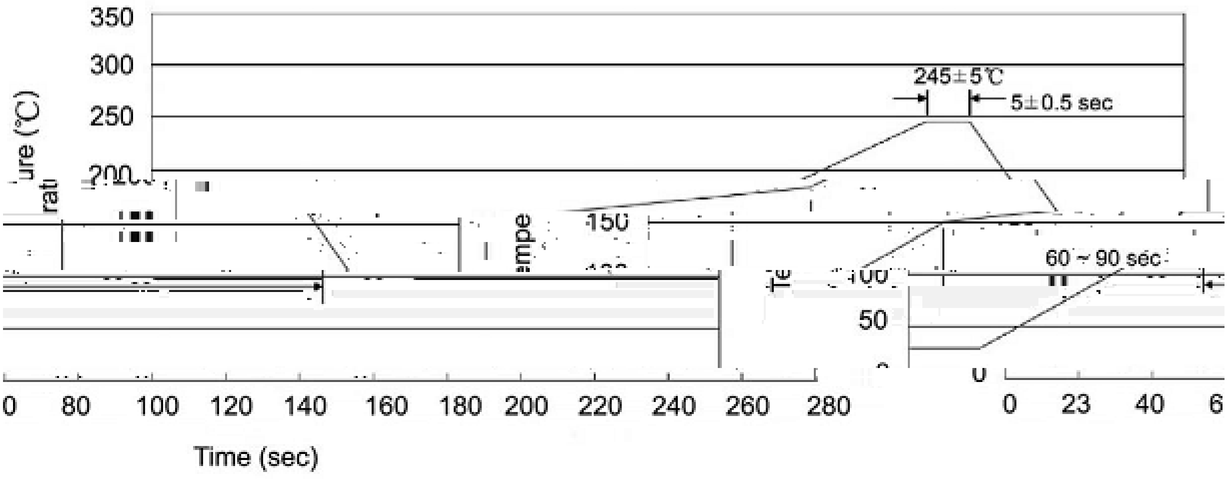

	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

˧ ü q ̄`Y Ţ / Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

ɘ ⊑ ⋞— / Packaging SPEC.

/ REEL

Package Type	Units					Dimension		(unit mm^3)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-89	1,000	7	7,000	8	56,000	7 ρ ×12		